DISCRETE SEMICONDUCTORS

DATA SHEET

BTA216B series D, E and F Three quadrant triacs guaranteed commutation

Product specification

July 2018



Three quadrant triacs guaranteed commutation

BTA216B series D, E and F

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a plastic envelope suitable for surface mounting, intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

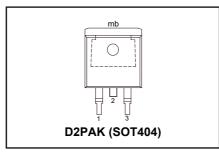
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BTA216B- BTA216B- BTA216B- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	600D 600E 600F 600 16 140	V A A

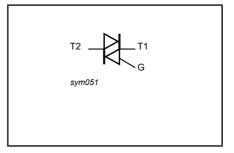
PINNING - SOT404

PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
mb	main terminal 2		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	600 ¹	V
I _{T(RMS)}	RMS on-state current Non-repetitive peak	full sine wave; T _{mb} ≤ 99 °C full sine wave;	-	16	А
l²t dl _⊤ /dt	on-state current I ² t for fusing Repetitive rate of rise of on-state current after	$\begin{split} & T_{j} = 25 \text{ °C prior to} \\ & \text{surge} \\ & t = 20 \text{ ms} \\ & t = 16.7 \text{ ms} \\ & t = 10 \text{ ms} \\ & I_{TM} = 20 \text{ A; } I_{G} = 0.2 \text{ A;} \\ & dI_{G}/dt = 0.2 \text{ A/}\mu\text{s} \end{split}$	-	140 150 98 100	Α Α Α²s Α/μs
$\begin{matrix} I_{GM} \\ P_{GM} \\ P_{G(AV)} \end{matrix}$	triggering Peak gate current Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- - -40 -	2 5 0.5 150 125	A W C C

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th } j\text{-mb}}$ $R_{\text{th } j\text{-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle minimum footprint, FR4 board	- - -	- - 55	1.2 1.7 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA216B-		D	Е	F	
I _{GT}	Gate trigger current ²	V _D = 12 V; I _T = 0.1 A T2+ G+ T2+ G- T2- G-	- - -	5 5 5	10 10 10	25 25 25	mA mA mA
I _L	Latching current	V _D = 12 V; I _{GT} = 0.1 A T2+ G+ T2+ G- T2- G-	- - -	15 25 25	25 30 30	30 40 40	mA mA mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	25	30	mA
					D, E, F		
$egin{array}{c} V_{T} \ V_{GT} \end{array}$	On-state voltage Gate trigger voltage	$I_T = 20 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$ $I_T = 125 \text{ °C}$	- - 0.25		1.5 1.5 -		>>>
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-		0.5		mA

DYNAMIC CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		MAX.	UNIT
		BTA216B-	D	E	F		
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110 °C;$ exponential waveform; gate open circuit	30	60	70	-	V/μs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C}; \ I_{T_{(RMS)}} = 16 \text{ A}; \ dV_{com}/dt = 10V/\mu s; gate$	2.5	6.2	18	-	A/ms
dl _{com} /dt	Critical rate of change of commutating current	open circuit $V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 0.1 \text{V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

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² Device does not trigger in the T2-, G+ quadrant.

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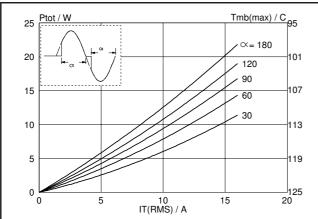


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

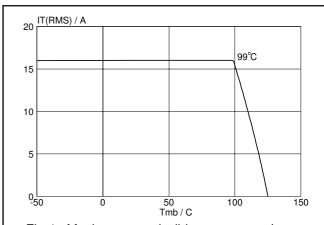


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

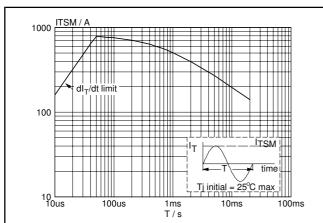


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

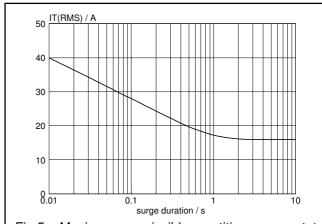


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 99 ^{\circ}C$.

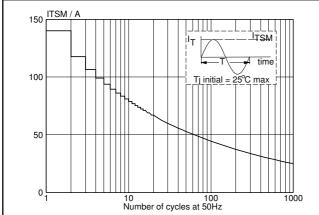


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

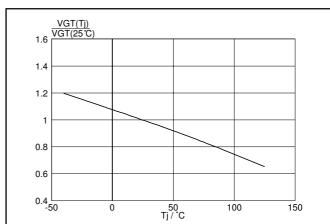
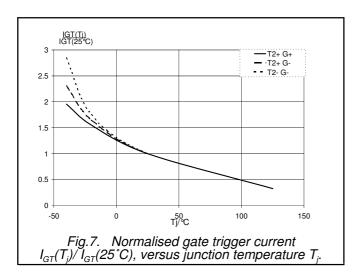
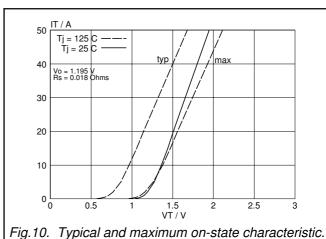


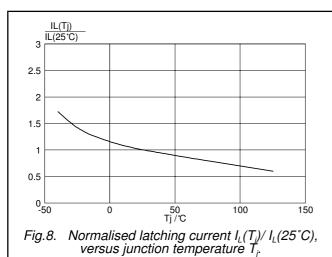
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_{j} .

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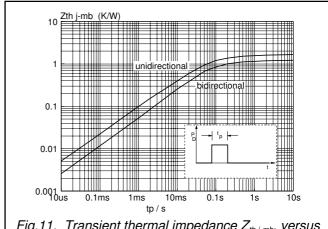


Fig.11. Transient thermal impedance $Z_{th j-mb}$, versus pulse width t_o.

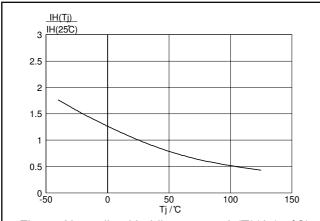


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

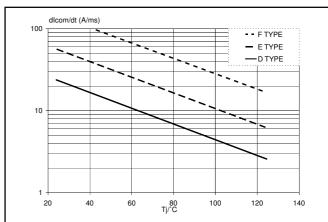
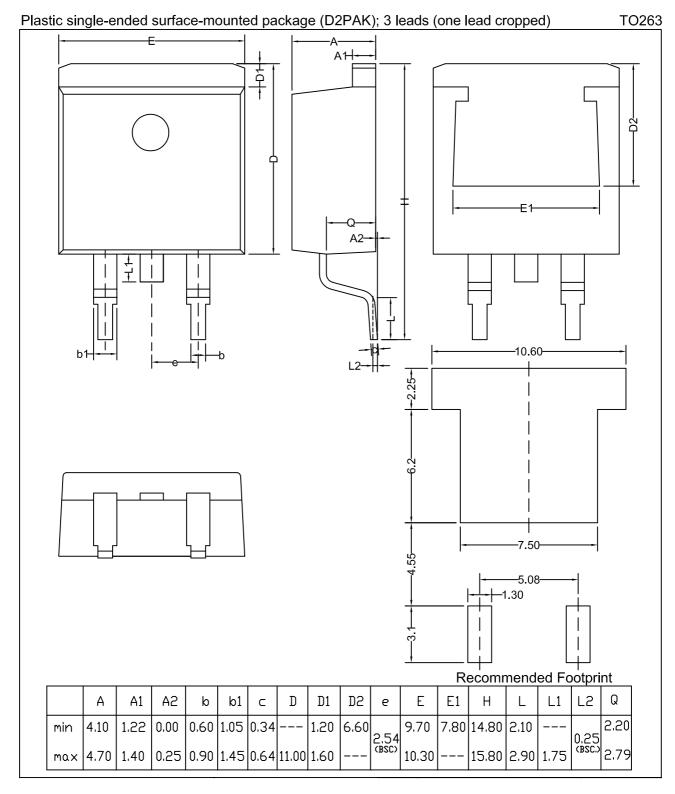


Fig.12. Mimimum, critical rate of change of commutating current dI_{com}/dt versus junction temperature, $dV_{com}/dt = 10V/\mu s$.

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MECHANICAL DATA



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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